

# THYRISTOR MODULE

# PFT814N

## 80A / 400V

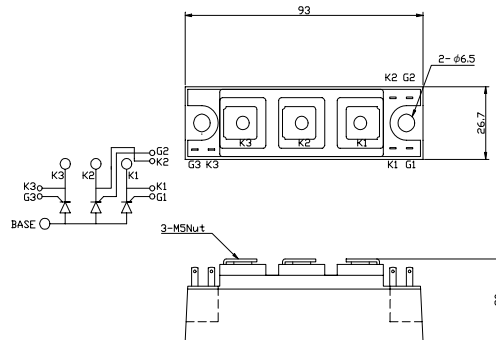
### FEATURES

- \* 3 Phase Anode Common  
Half Bridge Circuit
- \* High Surge Capability
- \* UL Recognized, File No. E187184

### TYPICAL APPLICATIONS

- \* Rectified For General Use

OUTLINE DRAWING



### Maximum Ratings

Approx Net Weight:150g

Parameter	Symbol	Grade	Unit
		PFT814N	
Repetitive Peak Off-State Voltage	$V_{DRM}$	400	V
Non Repetitive Peak Off-State Voltage	$V_{DSM}$	500	
Repetitive Peak Reverse Voltage	$V_{RRM}$	400	V
Non Repetitive Peak Reverse Voltage	$V_{RSM}$	500	

Parameter		Conditions	Max Rated Value	Unit	
Average Rectified Output Current	$I_{O(AV)}$	50Hz Half Sine Wave condition $T_c=121^{\circ}C$	80	A	
RMS On-State Current	$I_{T(RMS)}$		125	A	
Surge On-State Current	$I_{TSM}$	50 Hz Half Sine Wave, 1Pulse, Non-Repetitive	2300	A	
I Squared t	$I^2t$	2msec to 10msec	26400	$A^2s$	
Peak Gate Power	$P_{GM}$		5	W	
Average Gate Power	$P_{G(AV)}$		1	W	
Peak Gate Current	$I_{GM}$		2	A	
Peak Gate Voltage	$V_{GM}$		10	V	
Peak Gate Reverse Voltage	$V_{RGM}$		5	V	
Operating Junction Temperature Range	$T_{jw}$		-40 to +150	$^{\circ}C$	
Storage Temperature Range	$T_{stg}$		-40 to +125	$^{\circ}C$	
Mounting torque	Case mounting	Ftor	Greased M6 Screw	2.4 to 3.5	N.m
	Terminals		M5 Screw	2.4 to 2.8	

Value per 1 Arm

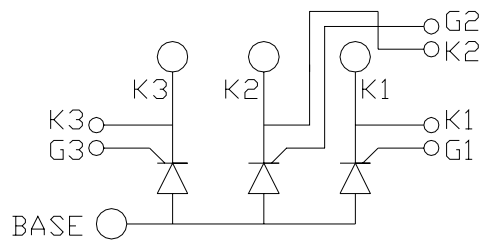
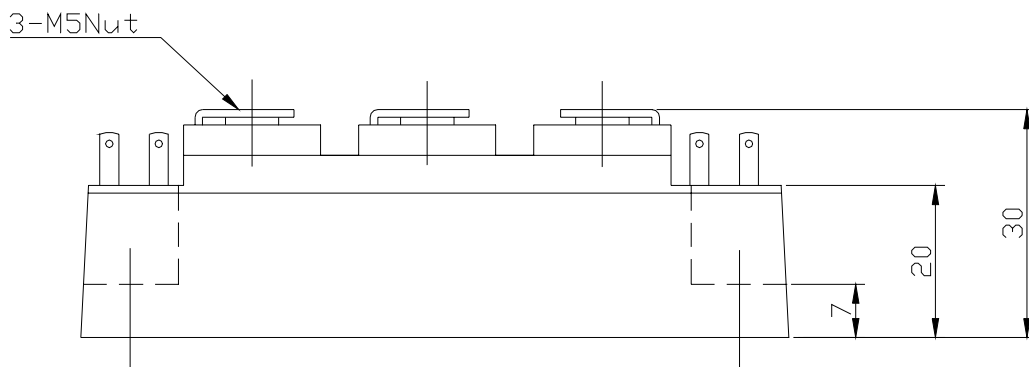
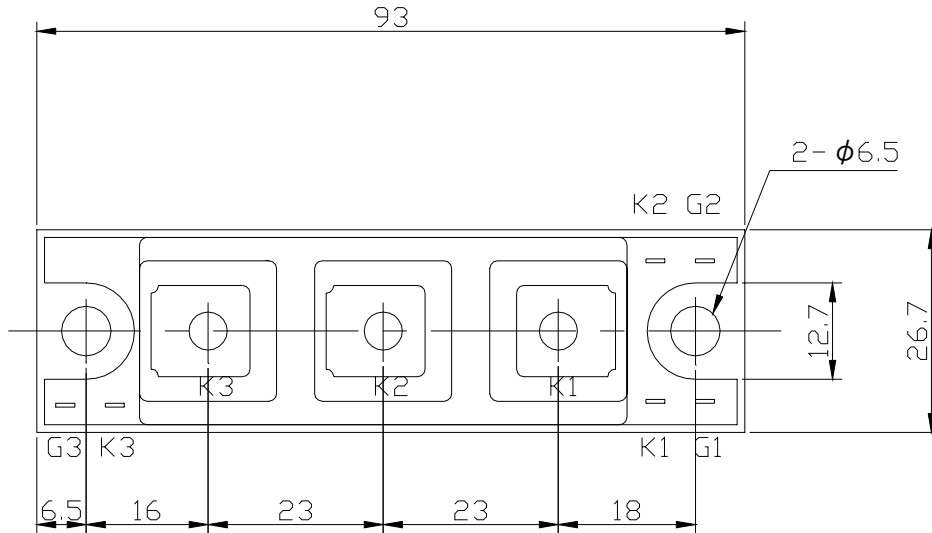
**Electrical • Thermal Characteristics**

Characteristics	Symbol	Test Conditions	Maximum Value.			Unit
			Min.	Typ.	Max.	
Peak Off-State Current	$I_{DM}$	$V_{DM} = V_{DRM}, T_j = 150^\circ\text{C}$			20	mA
Peak Reverse Current	$I_{RM}$	$V_{RM} = V_{RRM}, T_j = 150^\circ\text{C}$			20	mA
Peak Forward Voltage	$V_{TM}$	$I_{TM} = 240\text{A}, T_j = 25^\circ\text{C}$			1.20	V
Gate Current to Trigger	$I_{GT}$	$V_D = 6\text{V}, I_T = 1\text{A}$	$T_j = -40^\circ\text{C}$		200	mA
			$T_j = 25^\circ\text{C}$		100	
			$T_j = 125^\circ\text{C}$		50	
Gate Voltage to Trigger	$V_{GT}$	$V_D = 6\text{V}, I_T = 1\text{A}$	$T_j = -40^\circ\text{C}$		4	V
			$T_j = 25^\circ\text{C}$		2.5	
			$T_j = 125^\circ\text{C}$		1.5	
Gate Non-Trigger Voltage	$V_{GD}$	$V_D = 2/3V_{DRM}, T_j = 125^\circ\text{C}$	0.2			V
Latching Current	$I_L$	$T_j = 25^\circ\text{C}$		100		mA
Holding Current	$I_H$	$T_j = 25^\circ\text{C}$		50		mA
Thermal Resistance *1	$R_{th(j-c)}$	Junction to Case			0.1	$^\circ\text{C/W}$

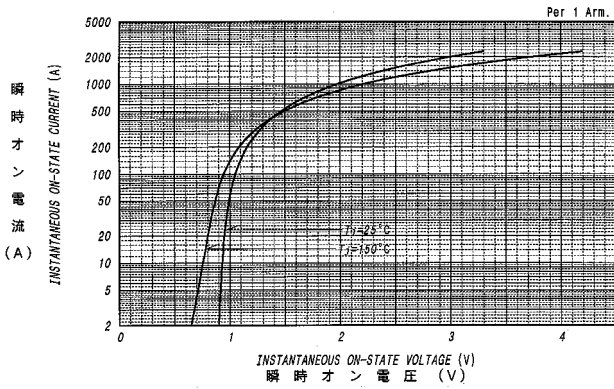
Value Per 1Arm

\*1:Value Per Module

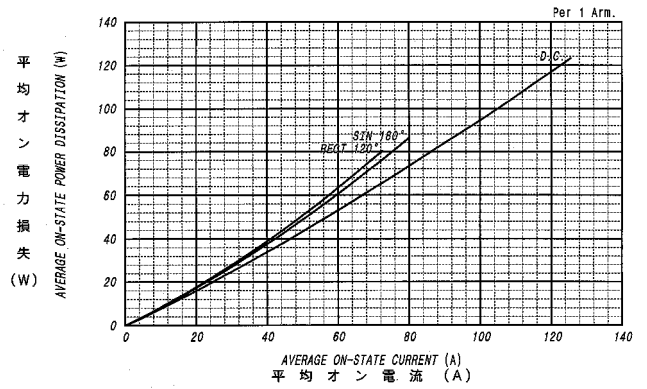
PFT814N OUTLINE DRAWING (Dimensions in mm)



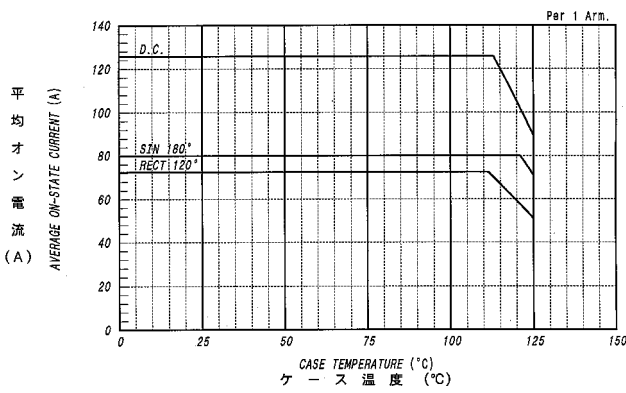
オン電圧特性  
ON-STATE CURRENT VS. VOLTAGE



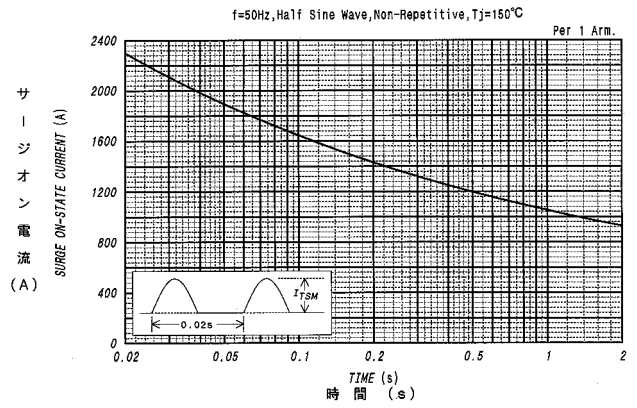
平均オン電力損失特性  
AVERAGE ON-STATE POWER DISSIPATION



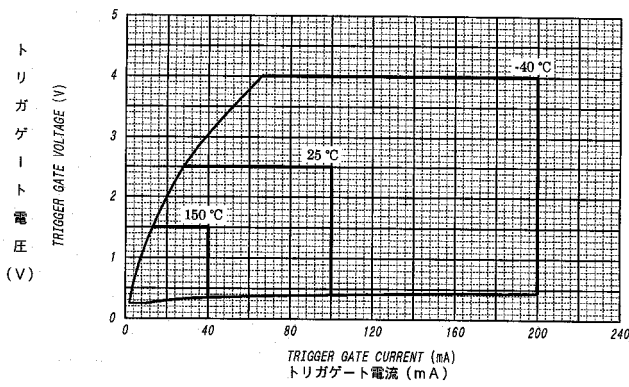
平均オン電流 - ケース温度定格  
AVERAGE ON-STATE CURRENT VS. CASE TEMPERATURE



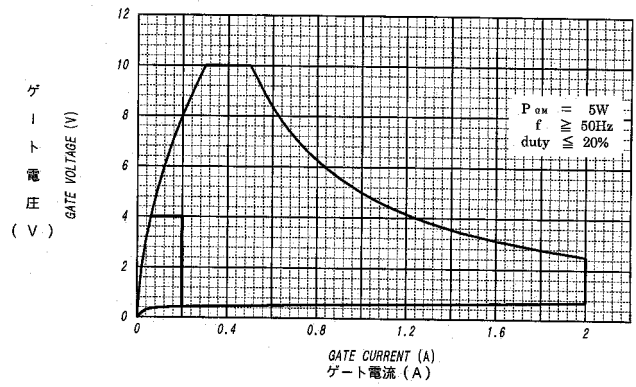
サージオン電流定格  
SURGE CURRENT RATINGS



ゲート特性  
GATE CHARACTERISTICS



ゲート定格  
GATE RATINGS



過渡熱抵抗特性  
MAXIMUM TRANSIENT THERMAL IMPEDANCE

